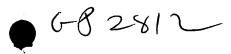
CS97-110/112 ·





December 11, 1998

issioner of Patents and Trademarks

Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572

20 McIntosh Drive

Poughkeepsie, N.Y. 12603

RECEIVED

DEC 2 2 1998

GROUP 2100

#3 I. D.S. F. M.Chulla 9/19/99

Subject:

Serial No. 09/186,388 11/05/98

B.H. Lee, Tang Ying, W.H. Rong, L.T. Hong, Zodig Lam

N TYPE IMPURITY DOPING USING IMPLANTATION OF P2+ IONS OR AS2+ IONS

Grp. Art Unit: 2812

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation. In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

S. Wolf et al, "Silicon Processing For The VLSI Era", Vol. 3, Lattice Press, Sunset Beach, CA, 1986, p. 327, discusses ion implantation using doubly charged species.

U.S. Patent 5,155,369 to Current, "Multiple Angle Implants For Shallow Implant", describes a method of using two doses of ions in an ion beam to provide implantation for shallow junction devices.

Sincerely,

Stephen B. Ackerman,

Reg. No. 37761